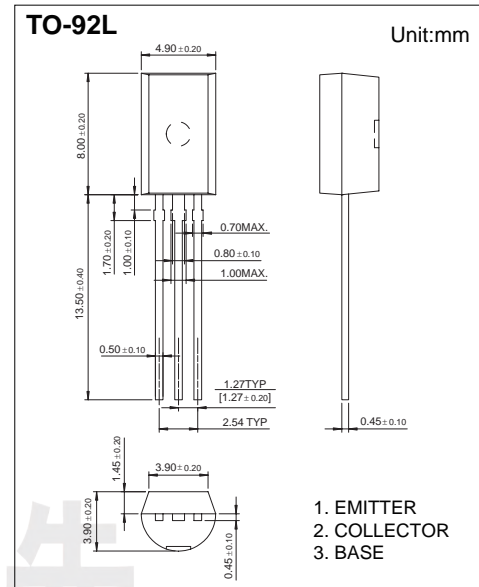


Transistor

PNP Transistors B772

■ Features

- High current output up to 3A
- Low saturation voltage
- Complement to D882



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	VCBO	-40	V
Collector - Emitter Voltage	VCEO	-30	
Emitter - Base Voltage	VEBO	-5	
Collector Current - Continuous	IC	-3	A
Peak Collector Current	ICP	-7	
Base Current	IB	-0.6	
Collector Power Dissipation	PC	0.5	W
Junction Temperature	TJ	150	°C
Storage Temperature	Tstg	-55 to 150	

PNP Transistors B772

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector- base breakdown voltage	VCBO	Ic= -100 μA, IE=0	-40			V
Collector- emitter breakdown voltage	VCEO	Ic= -1 mA, IB=0	-30			
Emitter - base breakdown voltage	VEBO	IE= -100 μA, IC=0	-5			
Collector cut-off current	ICBO	VCB= -30 V, IE=0			-1	μA
Collector cut-off current	ICEO	VCE=-30V, IB=0			-1	
Emitter cut-off current	IEBO	VEB= -3V, IC=0			-1	
Collector-emitter saturation voltage	VCE(sat)	Ic=-2 A, IB= -200mA			-0.5	V
Base - emitter saturation voltage	VBE(sat)	Ic=-2 A, IB= -200mA			-2	
DC current gain (Note.1)	hFE(1)	VCE= -2V, Ic= -20mA	30			
	hFE(2)	VCE= -2V, Ic= -1 A	100		400	
Output capacitance	Cob	VCB=-10V, IE=0, f=1MHz		45		pF
Transition frequency	fr	VCE= -5V, Ic= -100mA		80		MHz

Note.1:Pulse test: Pw<300μs, Duty Cycle<2%

■ Classification of hFE(2)

Rank	Q	P	E
Range	100-200	160-320	200-400

PNP Transistors B772

■ Typical Characteristics

